NIKO-SEM

N-Channel Enhancement Mode Field Effect Transistor

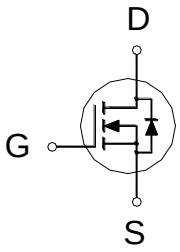
PD676BA

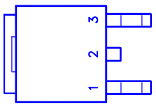
TO-252

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
40V	2.9mΩ	133A





1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[2]	T_C = 25 °C	I_D	130	A
	T_C = 100 °C		82	
Continuous Drain Current[2]	T_A = 25 °C	I_D	19	
	T_A = 100 °C		15	
Pulsed Drain Current[1]		I_{DM}	250	
Avalanche Current		I_{AS}	67	
Avalanche Energy	L = 0.1mH	E_{AS}	227	mJ
Power Dissipation	T_C = 25 °C	P_D	83	W
	T_C = 100 °C		33	
Power Dissipation	T_A = 25 °C	P_D	2	
	T_A = 100 °C		1.28	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	° C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		1.5	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

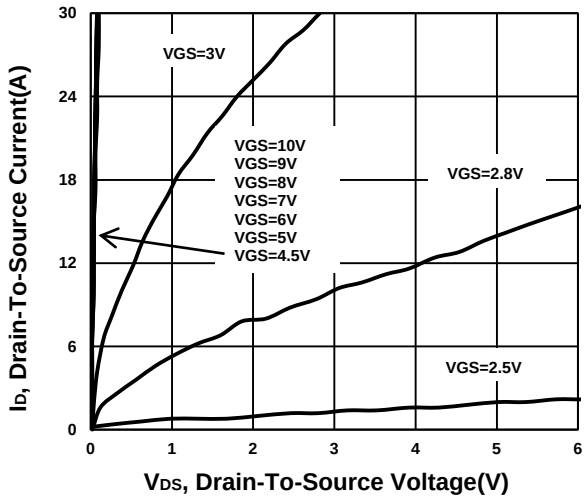
[1]Pulse width limited by maximum junction temperature.
[2]Package limitation current is 85A.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

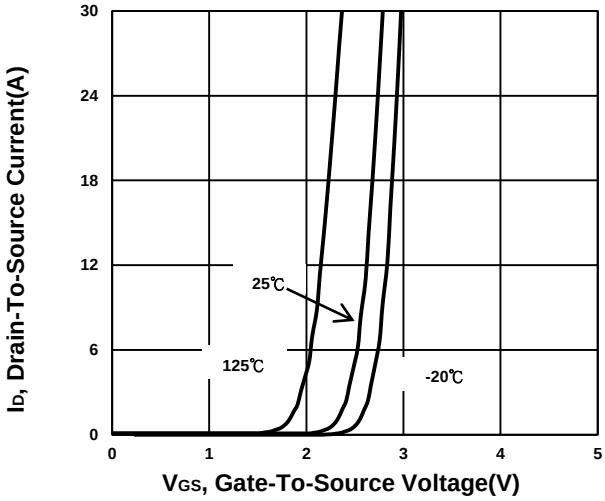
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS MIN	LIMITS TYP	LIMITS MAX	UNITS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.7	2.3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 32V, V_{GS} = 0V			1	μA
		V_{DS} = 30V, V_{GS} = 0V, T_J = 125 °C			10	μA
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 16A		2.6	3.7	mΩ
		V_{GS} = 10V, I_D = 20A		2.3	2.9	mΩ
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		105		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz		6266		pF
Output Capacitance	C_{oss}			705		pF
Reverse Transfer Capacitance	C_{rss}			412		pF
Gate Resistance	Rg	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.5		Ω
Total Gate Charge[2]	$Q_{g(VGS=10V)}$	V_{DS} =20V,I_D = 20A		117		nC
	$Q_{g(VGS=4.5V)}$			59		nC
Gate-Source Charge[2]	Q_{gs}			19		nC
Gate-Drain Charge[2]	Q_{gd}			24		nC
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 20V, I_D ≅ 20A, V_{GS} = 10V, R_{GEN} =6Ω		30		nS
Rise Time[2]	t_r			100		nS
Turn-Off Delay Time[2]	$t_{d(off)}$			174		nS
Fall Time[2]	t_f			158		nS
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				64	A
Forward Voltage[1]	V_{SD}	I_F = 20A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 20A, dIs/dt= 100A/μs		40		nS
Reverse Recovery Charge	Q_{rr}			28		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

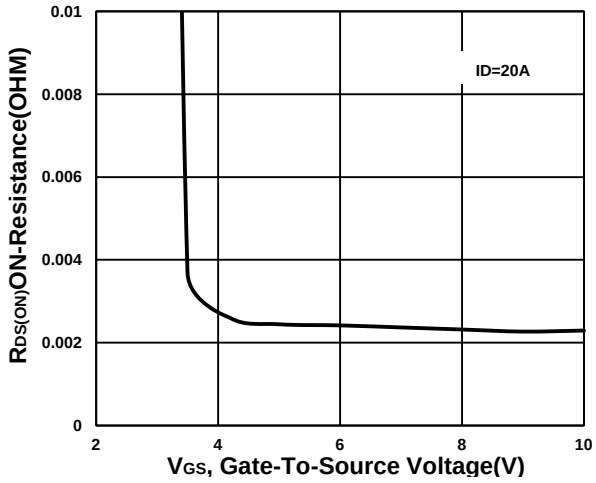
Output Characteristics



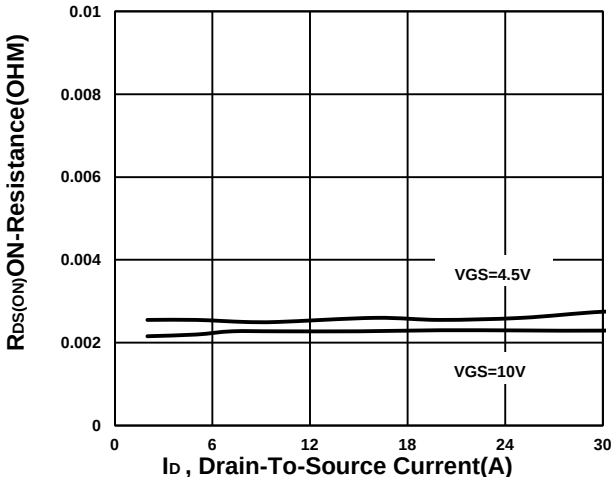
Transfer Characteristics



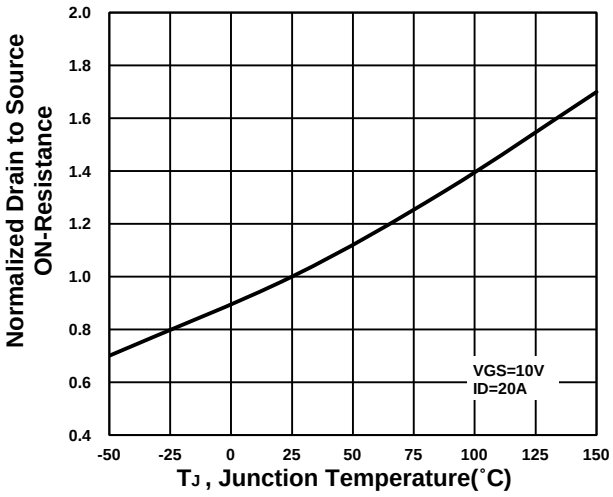
On-Resistance VS Gate-To-Source Voltage



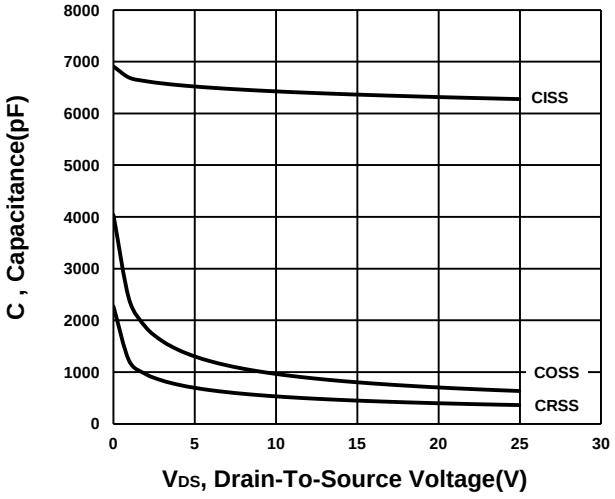
On-Resistance VS Drain Current



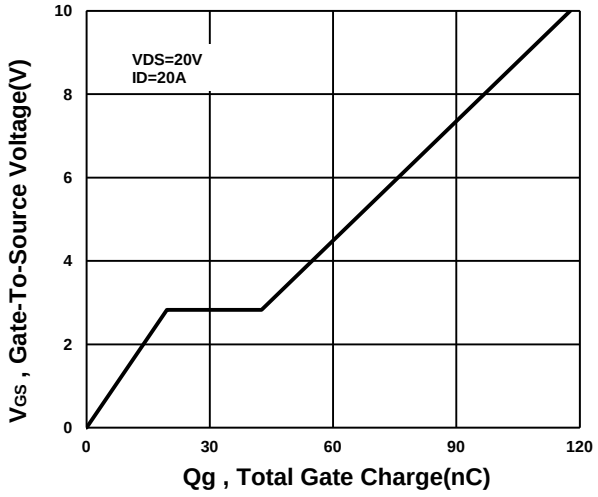
On-Resistance VS Temperature



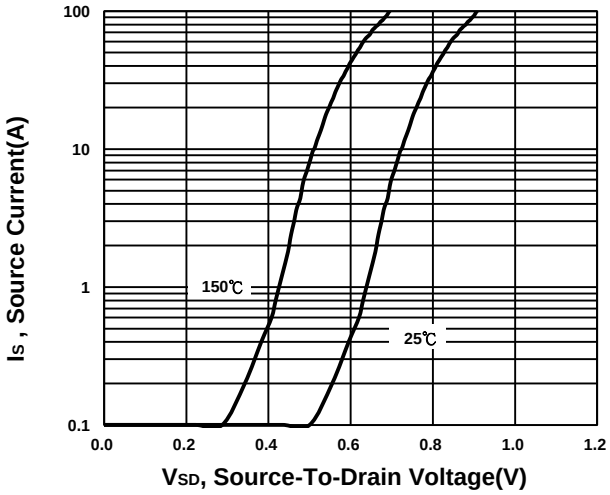
Capacitance Characteristic



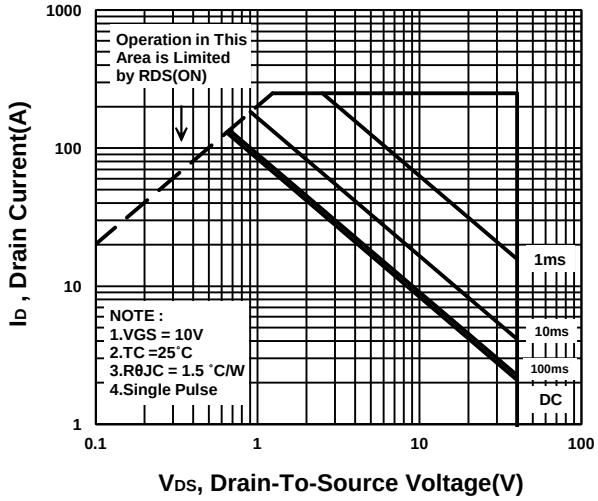
Gate charge Characteristics



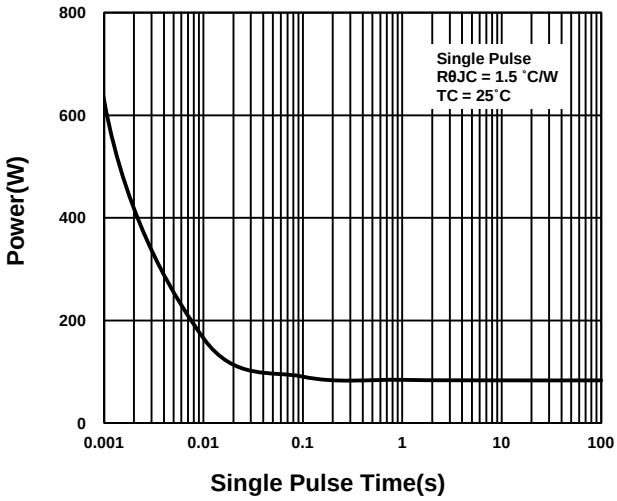
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve